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October 2013

FQB27P06

P-Channel QFET® MOSFET

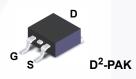
-60 V, -27 A, 70 mΩ

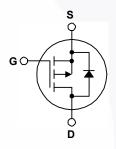
Description

This P-Channel enhancement mode power MOSFET is \cdot -27 A, -60 V, $R_{DS(on)}$ = 70 m Ω (Max) @V_{GS} = -10 V, produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, audio amplifier, DC motor control, and variable switching power applications.

Features

- $I_D = -13.5 A$
- Low Gate Charge (Typ. 33 nC)
- · Low Crss (Typ. 120 pF)
- · 100% Avalanche Tested
- 175°C Maximum Junction Temperature Rating





Absolute Maximum Ratings $T_C = 25^{\circ}C$ unless otherwise noted

Symbol	Parameter		FQB27P06TM	Unit	
V _{DSS}	Drain-Source Voltage		-60	V	
I _D	Drain Current - Continuous (T _C = 25°C) - Continuous (T _C = 100°C)		-27	Α	
			-19.1	А	
I _{DM}	Drain Current - Pulsed	(Note 1)	-108	A	
V_{GSS}	Gate-Source Voltage		± 25	V	
E _{AS}	Single Pulsed Avalanche Energy	(Note 2)	560	mJ	
I _{AR}	Avalanche Current	(Note 1)	-27	А	
E _{AR}	Repetitive Avalanche Energy	(Note 1)	12	mJ	
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	-7.0	V/ns	
P _D	Power Dissipation (T _A = 25°C) *		3.75	W	
	Power Dissipation (T _C = 25°C)		120	W	
	- Derate above 25°C		0.8	W/°C	
T_J , T_{STG}	Operating and Storage Temperature Range		-55 to +175	°C	
T _L	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds		300	°C	

Thermal Characteristics

Symbol	Parameter	FQB27P06TM	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max. 1.25		
Rou	Thermal Resistance, Junction to Ambient (minimum pad of 2 oz copper), Max.	62.5	°C/W
	Thermal Resistance, Junction to Ambient (* 1 in ² pad of 2 oz copper), Max.	40	

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity	
FQB27P06	FQB27P06TM	D2-PAK	330mm	24mm	800	

Elorical Characteristics

Symbol	Parameter	Test Conditions	Min	Тур	Max	Unit
Off Cha	aracteristics					
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$	-60			V
ΔBV _{DSS} / ΔT _J	Breakdown Voltage Temperature Coefficient	I_D = -250 μ A, Referenced to 25°C		-0.06		V/°C
I _{DSS}	Onto Welliams D	V _{DS} = -60 V, V _{GS} = 0 V			-1	μА
	Zero Gate Voltage Drain Current	V _{DS} = -48 V, T _C = 150°C			-10	μΑ
I _{GSSF}	Gate-Body Leakage Current, Forward	V _{GS} = -25 V, V _{DS} = 0 V			-100	nA
I _{GSSR}	Gate-Body Leakage Current, Reverse	V _{GS} = 25 V, V _{DS} = 0 V			100	nA
On Cha	racteristics					
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	-2.0		-4.0	V
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} = -10 V, I _D = -13.5 A		0.055	0.07	Ω
9 _{FS}	Forward Transconductance	$V_{DS} = -30 \text{ V}, I_{D} = -13.5 \text{ A}$		12.4		S
	ic Characteristics					
C _{iss}	Input Capacitance	$V_{DS} = -25 \text{ V}, V_{GS} = 0 \text{ V},$ f = 1.0 MHz		1100	1400	pF
C _{oss}	Output Capacitance			510	660	pF
C _{rss}	Reverse Transfer Capacitance			120	155	pF
Switchi	ing Characteristics					
t _{d(on)}	Turn-On Delay Time	$V_{DD} = -30 \text{ V}, I_{D} = -13.5 \text{ A},$		18	45	ns
t _r	Turn-On Rise Time	$R_G = 25 \Omega$		185	380	ns
t _{d(off)}	Turn-Off Delay Time	11.6 - 20 32		30	70	ns
t _f	Turn-Off Fall Time	(Note 4)		90	190	ns
Qg	Total Gate Charge	V _{DS} = -48 V, I _D = -27 A,		33	43	nC
Q _{gs}	Gate-Source Charge	V _{GS} = -10 V	/	6.8		nC
Q _{gd}	Gate-Drain Charge	(Note 4)		18		nC
Drain-S	Source Diode Characteristics ar	nd Maximum Ratings				
I _S	Maximum Continuous Drain-Source Diode Forward Current				-27	Α
I _{SM}	Maximum Pulsed Drain-Source Diode F	Forward Current			-108	Α
V _{SD}	Drain-Source Diode Forward Voltage	V _{GS} = 0 V, I _S = -27 A			-4.0	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0 V, I _S = -27 A,		105		ns
Q _{rr}	Reverse Recovery Charge	dl _F / dt = 100 A/μs		0.41		μС

- Notes:
 1. Repetitive Rating : Pulse width limited by maximum junction temperature
 2. L = 0.9mH, I_{AS} = -27A, V_{DD} = -25V, R_G = 25 Ω , Starting T_J = 25°C
 3. I_{SD} \leq -27A, di/dt \leq 300A/µs, V_{DD} \leq BV_{DSS}, Starting T_J = 25°C
 4. Essentially independent of operating temperature

Typical Characteristics

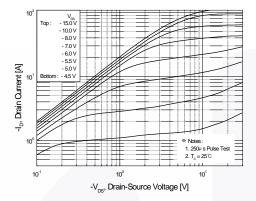


Figure 1. On-Region Characteristics

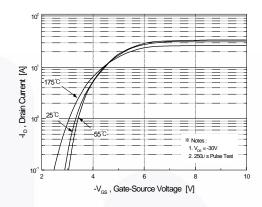


Figure 2. Transfer Characteristics

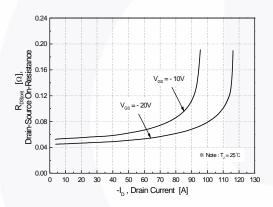


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

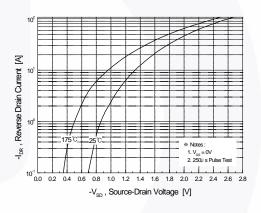


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

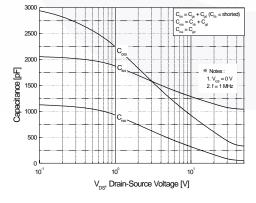


Figure 5. Capacitance Characteristics

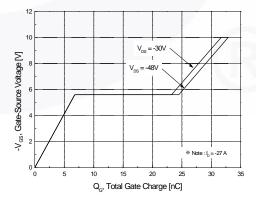


Figure 6. Gate Charge Characteristics

Typical Characteristics (Continued)

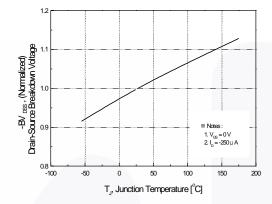


Figure 7. Breakdown Voltage Variation vs. Temperature

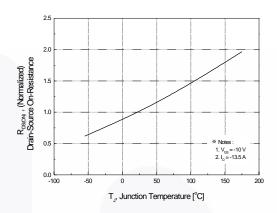


Figure 8. On-Resistance Variation vs. Temperature

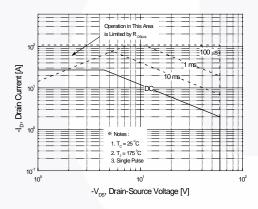


Figure 9. Maximum Safe Operating Area

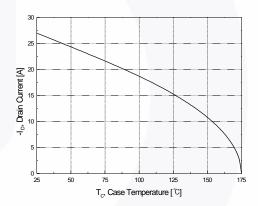


Figure 10. Maximum Drain Current vs. Case Temperature

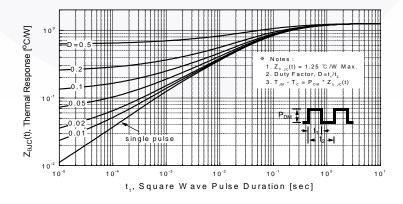


Figure 11. Transient Thermal Response Curve



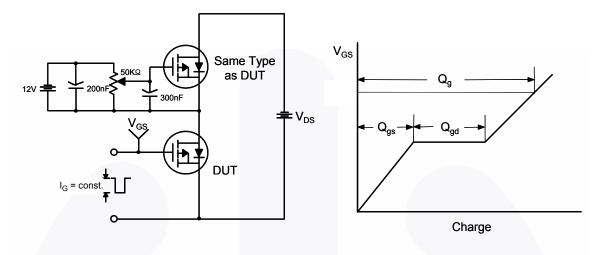


Figure 13. Resistive Switching Test Circuit & Waveforms

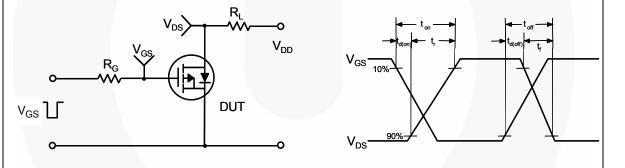
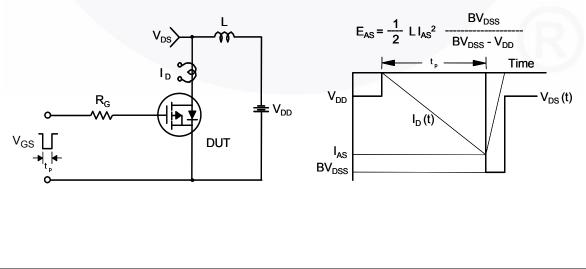
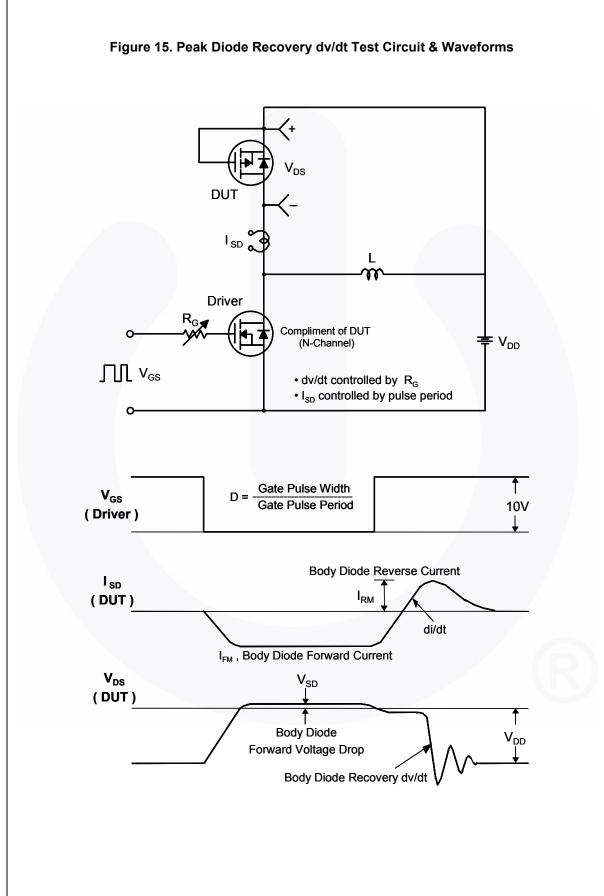


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms





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Mechanical Dimensions

TO-263 2L (D²PAK)

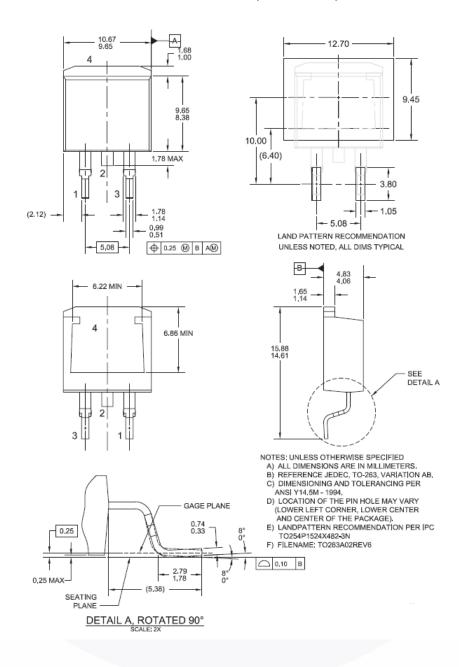


Figure 16. 2LD, TO263, Surface Mount

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Dimension in Millimeters





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Наши контакты:

Телефон: +7 812 627 14 35

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Адрес: 198099, Санкт-Петербург,

Промышленная ул, дом № 19, литера Н,

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